

HIGH EFFICIENCY ULTRAFAST DIODE

Table 1: Main Product Characteristics

$I_{F(AV)}$	2 A
V_{RRM}	600 V
T_j	175°C
V_F (typ)	1 V
t_{rr} (typ)	35 ns

FEATURES AND BENEFITS

- Very low conduction losses
- Negligible switching losses
- Low forward and reverse recovery times
- High junction temperature

DESCRIPTION

The STTH2R06 is using ST Turbo 2 600V planar Pt doping technology. It is specially suited for switching mode base drive & transistor circuits. Packaged in axial, SMA, SMB and SMC, this device is intended for use in high frequency inverters, free wheeling and polarity protection.

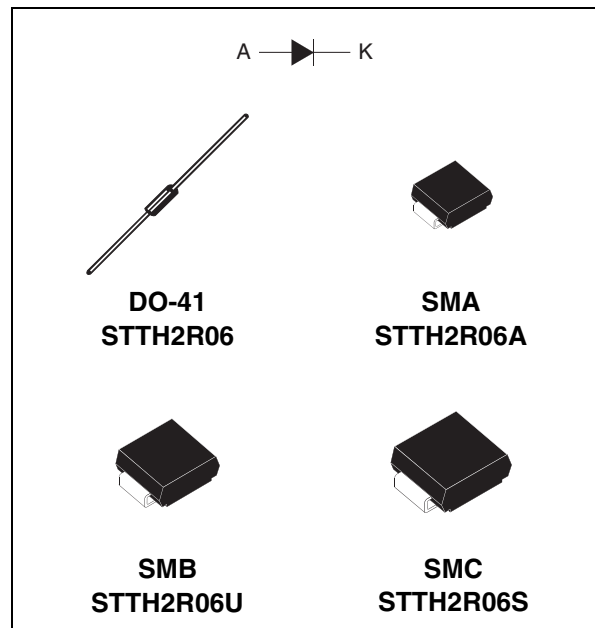


Table 2: Order Codes

Part Number	Marking
STTH2R06	STTH2R06
STTH2R06RL	STTH2R06
STTH2R06A	R6A
STTH2R06U	R6U
STTH2R06S	R62

Table 3: Absolute Ratings (limiting values)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			600	V
$I_{F(RMS)}$	RMS forward voltage			7	A
$I_{F(AV)}$	Average forward current $\delta = 0.5$	DO-41	$T_L = 70^\circ\text{C}$	2	A
		SMA	$T_L = 85^\circ\text{C}$		
		SMB	$T_L = 100^\circ\text{C}$		
		SMC	$T_L = 115^\circ\text{C}$		
I_{FSM}	Surge non repetitive forward current	DO-41	$t_p = 10\text{ms}$	40	A
		SMA / SMB / SMC	sinusoidal	30	
T_{stg}	Storage temperature range			-65 to + 175	°C
T_j	Operating junction temperature range			-40 to + 175	°C

Table 4: Thermal Resistance

Symbol	Parameter		Value (max).	Unit
$R_{th(j-l)}$	Junction to lead	DO-41 L = 5 mm	35	°C/W
		SMA	30	
		SMB	25	
		SMC	20	

Table 5: Static Electrical Characteristics

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			2	μA
		$T_j = 150^\circ\text{C}$			12	85	
V_F^{**}	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 2\text{A}$			1.7	V
		$T_j = 150^\circ\text{C}$			1.0	1.25	

Pulse test: * $t_p = 5\text{ ms}$, $\delta < 2\%$

** $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation: $P = 1 \times I_{F(AV)} + 0.125 I_F^2(RMS)$

Table 6: Dynamic Characteristics

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
t_{rr}	Reverse recovery time	$T_j = 25^\circ\text{C}$	$I_F = 0.5\text{A}$ $I_{rr} = 0.25\text{A}$ $I_R = 1\text{A}$			30	ns
			$I_F = 1\text{A}$ $dl_F/dt = -50\text{ A}/\mu\text{s}$ $V_R = 30\text{V}$		35	50	
t_{fr}	Forward recovery time	$T_j = 25^\circ\text{C}$	$I_F = 2\text{A}$ $dl_F/dt = 100\text{ A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$			100	ns
V_{FP}	Forward recovery voltage					10	V

Figure 1: Conduction losses versus average forward current

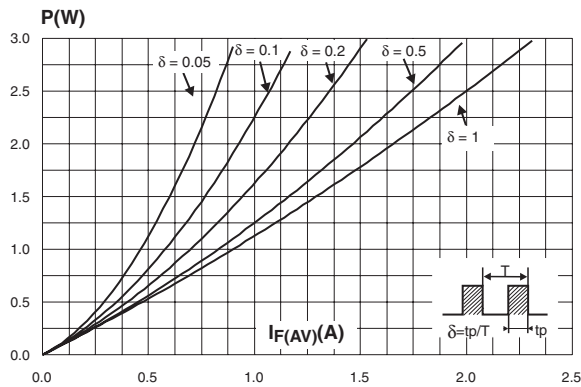


Figure 2: Forward voltage drop versus forward current

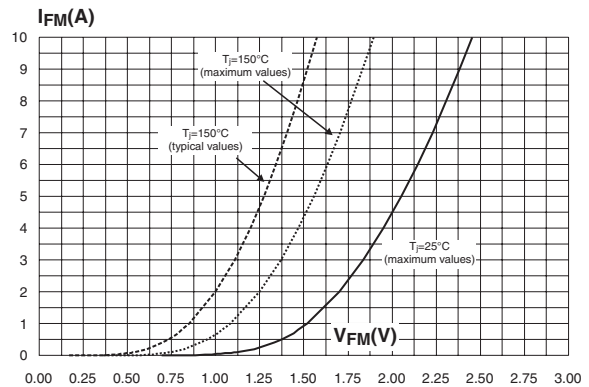


Figure 3: Relative variation of thermal impedance junction to case versus pulse duration (SMA/SMB/SMC: $S_{CU} = 1\text{cm}^2$)

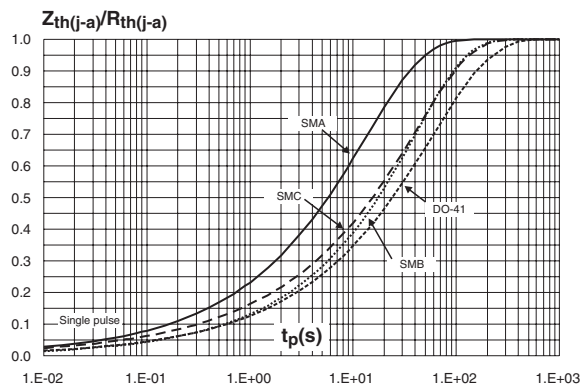


Figure 4: Peak reverse recovery current versus di_F/dt (typical values)

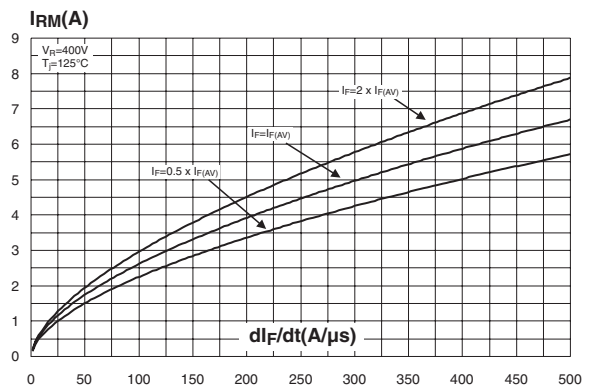


Figure 5: Reverse recovery time versus di_F/dt (typical values)

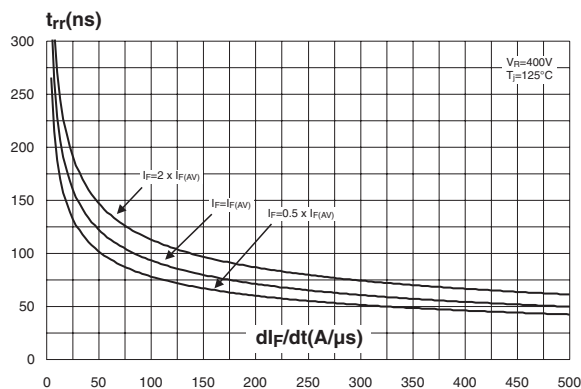


Figure 6: Reverse recovery charges versus di_F/dt (typical values)

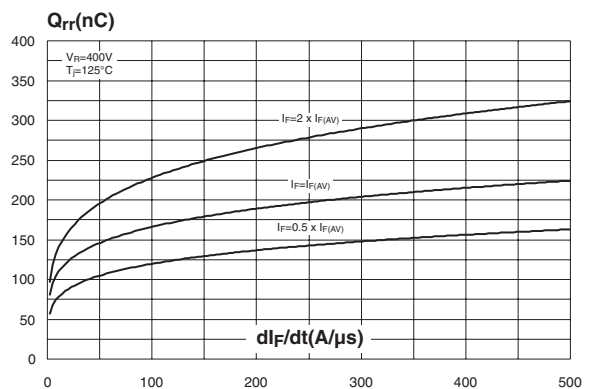


Figure 7: Relative variations of dynamic parameters versus junction temperature

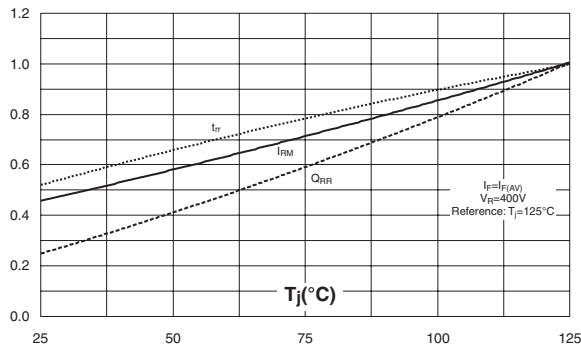


Figure 8: Transient peak forward voltage versus di_F/dt (typical values)

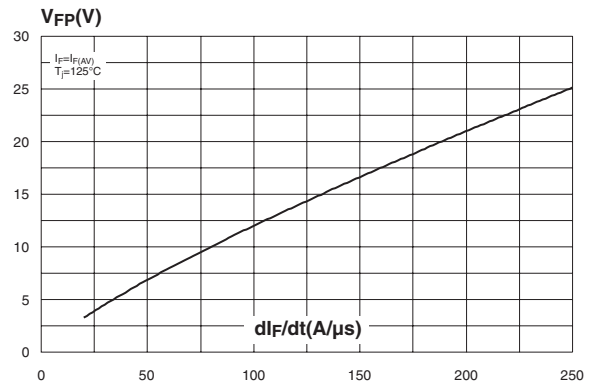


Figure 9: Forward recovery time versus di_F/dt (typical values)

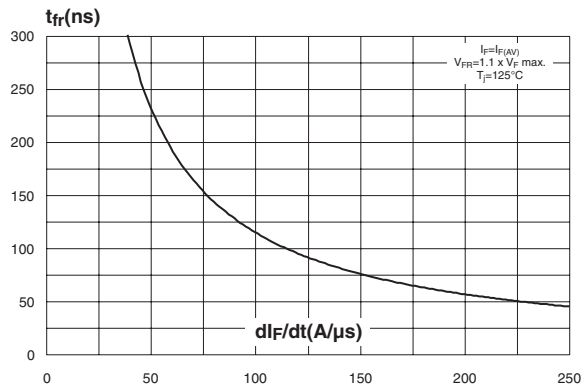


Figure 10: Junction capacitance versus reverse voltage applied (typical values)

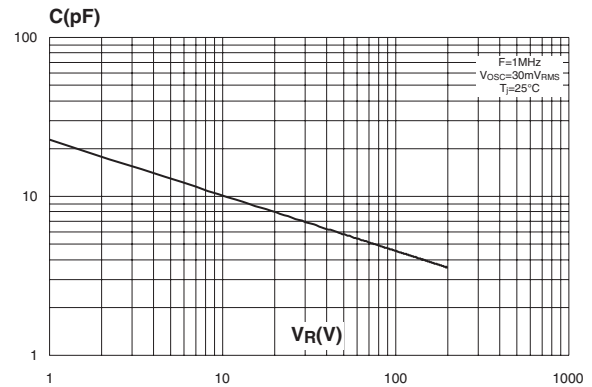


Figure 11: Thermal resistance junction to ambient versus copper surface under each lead (epoxy FR4, $e_{CU}=35\mu\text{m}$) (SMA/SMB/SMC)

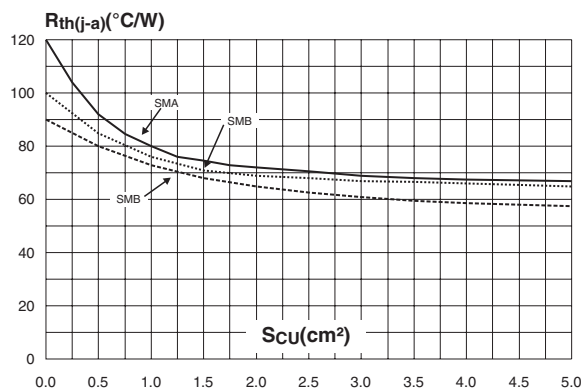


Figure 12: Thermal resistance versus lead length (DO-41)

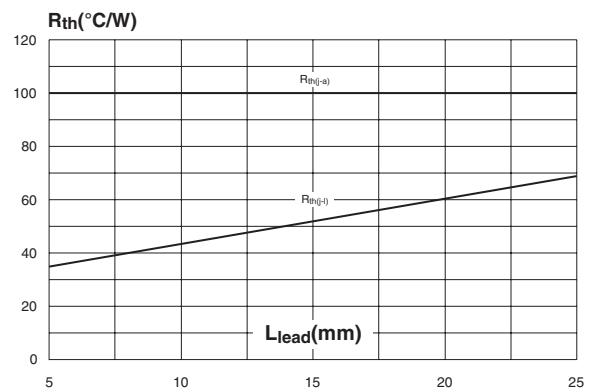


Figure 13: SMA Package Mechanical Data

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A1	1.90	2.03	0.075	0.080
A2	0.05	0.20	0.002	0.008
b	1.25	1.65	0.049	0.065
c	0.15	0.41	0.006	0.016
E	4.80	5.60	0.189	0.220
E1	3.95	4.60	0.156	0.181
D	2.25	2.95	0.089	0.116
L	0.75	1.60	0.030	0.063

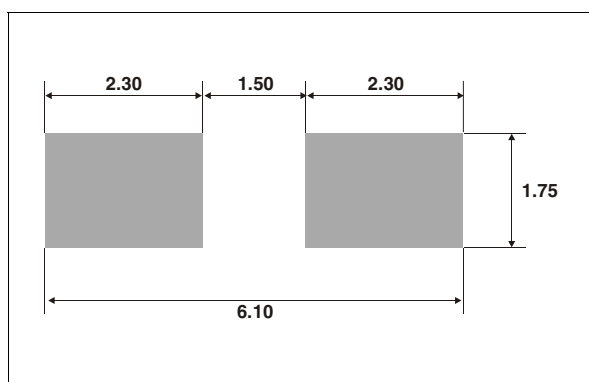
Figure 14: SMA Foot Print Dimensions
(in millimeters)

Figure 15: SMB Package Mechanical Data

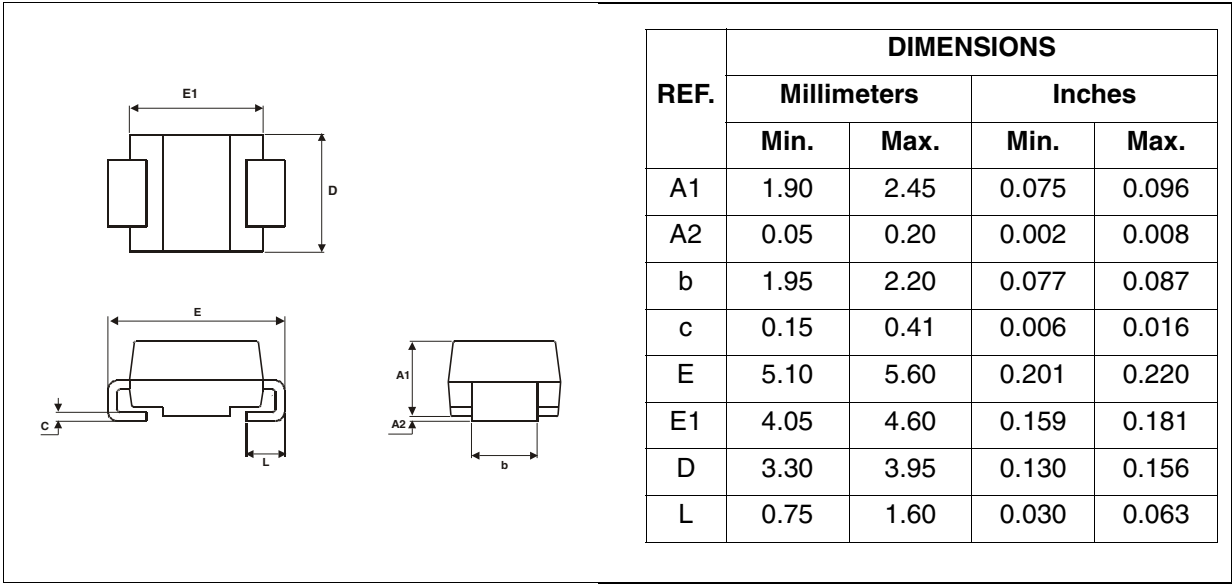


Figure 16: SMB Foot Print Dimensions
(in millimeters)

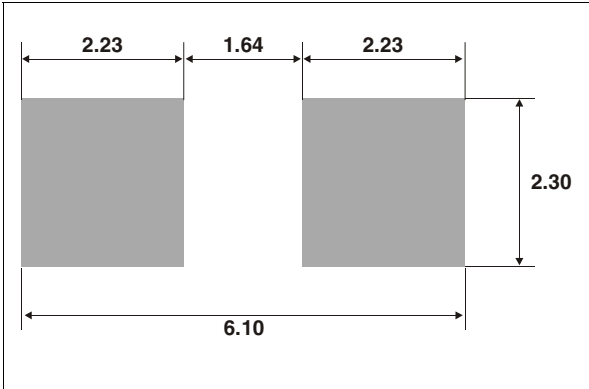
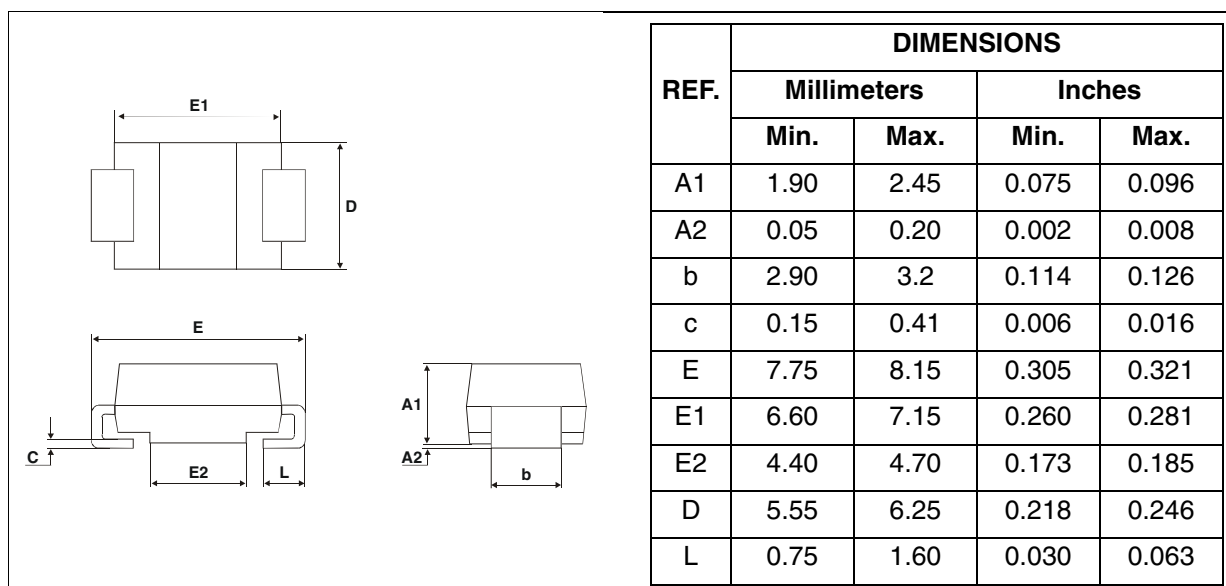
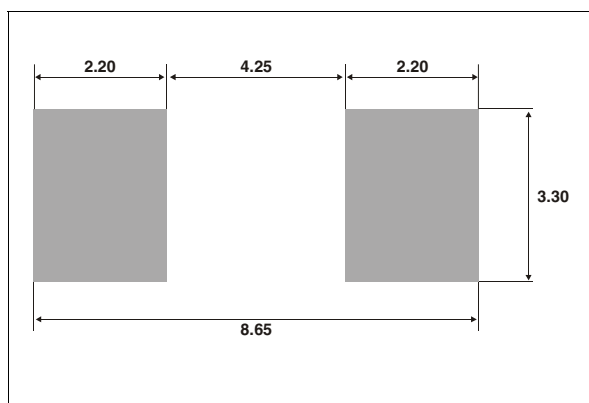


Figure 17: SMC Package Mechanical Data**Figure 18: SMC Foot Print Dimensions**
(in millimeters)

STTH2R06

Figure 19: DO-41 Package Mechanical Data

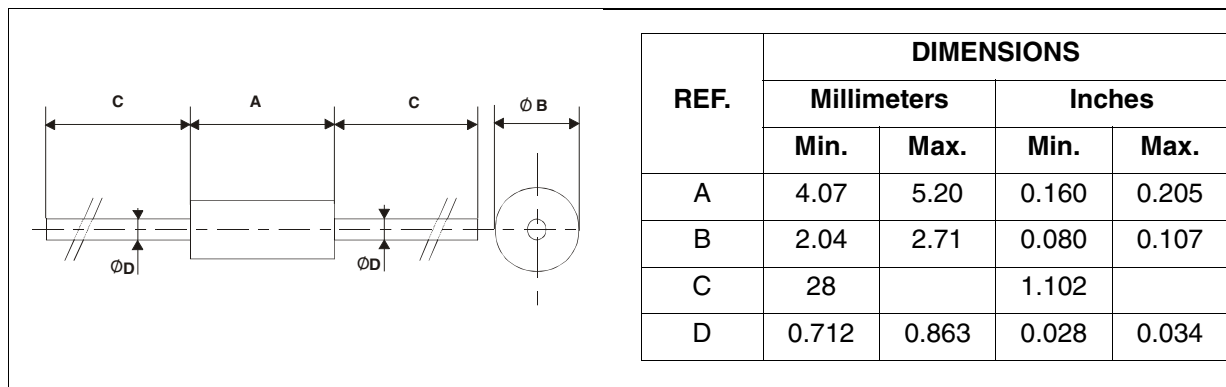


Table 7: Ordering Information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
STTH2R06	STTH2R06	DO-41	0.34 g	2000	Ammopack
STTH2R06RL	STTH2R06	DO-41	0.34 g	5000	Tape & reel
STTH2R06A	R6A	SMA	0.068 g	5000	Tape & reel
STTH2R06U	R6U	SMB	0.11 g	2500	Tape & reel
STTH2R06S	R62	SMC	0.243 g	2500	Tape & reel

Table 8: Revision History

Date	Revision	Description of Changes
07-Sep-2004	1	First issue.
1-Jun-2005	2	SMC package addition.

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